

HAT2085R

Silicon N Channel MOS FET
High Speed Power Switching

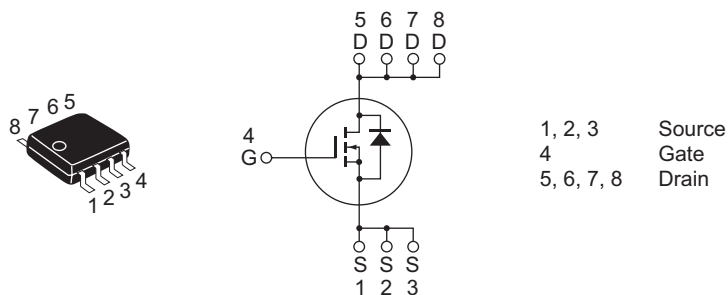
REJ03G1181-0200
(Previous: ADE-208-1232)
Rev.2.00
Sep 07, 2005

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8 <FP-8DAV>)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DS}	200	V
Gate to source voltage	V_{GS}	±30	V
Drain current	I_D	2	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	16	A
Body to drain diode reverse drain current	I_{DR}	2	A
Channel dissipation	P_{ch} ^{Note 2}	2.5	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$ 2. When using the glass epoxy board (FR4 40 × 40 × 1.6 mm), $PW \leq 10 s$

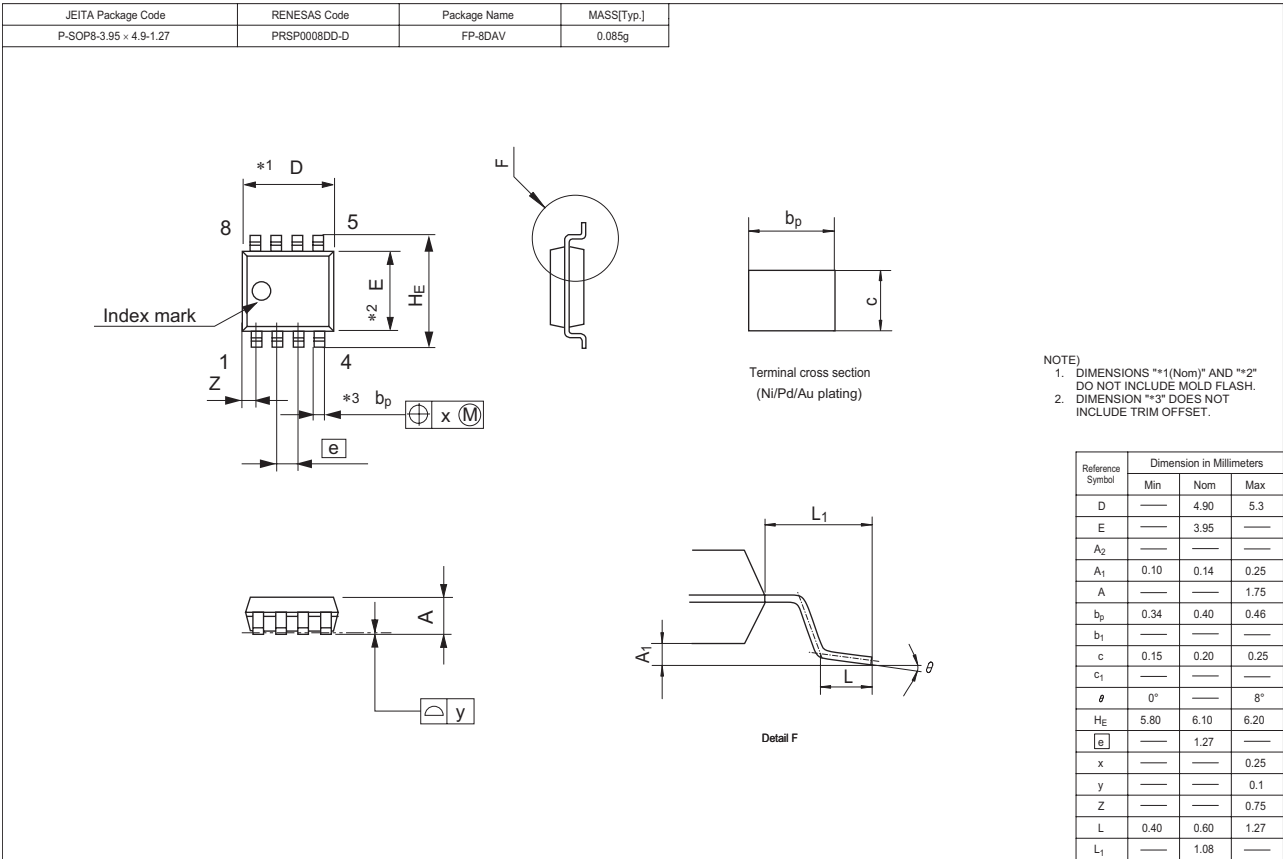
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR) DSS}$	200	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±0.1	μA	$V_{GS} = \pm 30 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1	μA	$V_{DS} = 200 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.49	0.64	Ω	$I_D = 1 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	1.2	2.0	—	S	$I_D = 1 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note 3}
Input capacitance	C_{iss}	—	300	—	pF	$V_{DS} = 25 \text{ V}$
Output capacitance	C_{oss}	—	43	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	12	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	21	—	ns	$V_{DD} = 100 \text{ V}$, $I_D = 1 \text{ A}$
Rise time	t_r	—	12	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	45	—	ns	$R_L = 100 \Omega$
Fall time	t_f	—	10.5	—	ns	$R_g = 10 \Omega$
Total gate charge	Q_g	—	10.2	—	nC	$V_{DD} = 160 \text{ V}$
Gate to source charge	Q_{gs}	—	1.8	—	nC	$V_{GS} = 10 \text{ V}$
Gate to drain charge	Q_{gd}	—	4.8	—	nC	$I_D = 2 \text{ A}$
Body to drain diode forward voltage	V_{DF}	—	0.8	1.2	V	$I_F = 2 \text{ A}$, $V_{GS} = 0$ ^{Note 3}
Body to drain diode reverse recovery time	t_{rr}	—	75	—	ns	$I_F = 2 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu s$

Note: 3. Pulse test

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
HAT2085R-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510